

# Some I-V and Noise Measurements

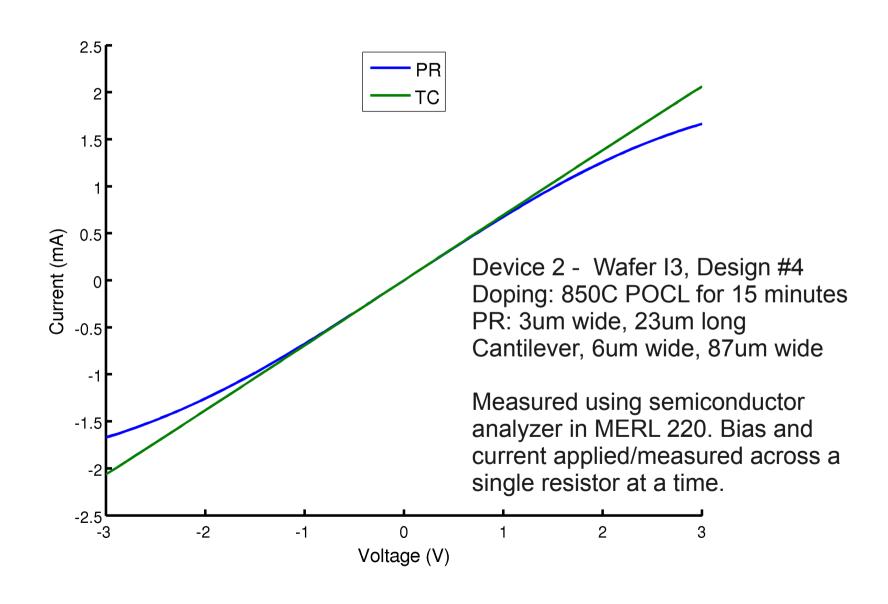
Joey Doll Dec. 22, 2009

A vaporized PR/PE cantilever

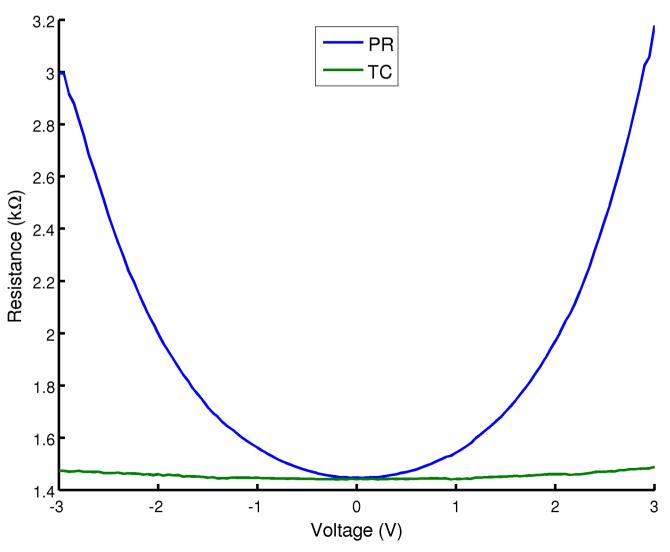
### Overview

- Have been measuring I-V curves and noise of my 340nm thick PR devices
- I haven't seen this in all of my measurements, need to figure out what has changed
- Strong thermal effects are seen in both I-V and noise characteristics
- Just wanted to share the curves and plan on doing more measurements eventually

### Typical I-V Curve



# Typical R Calculation

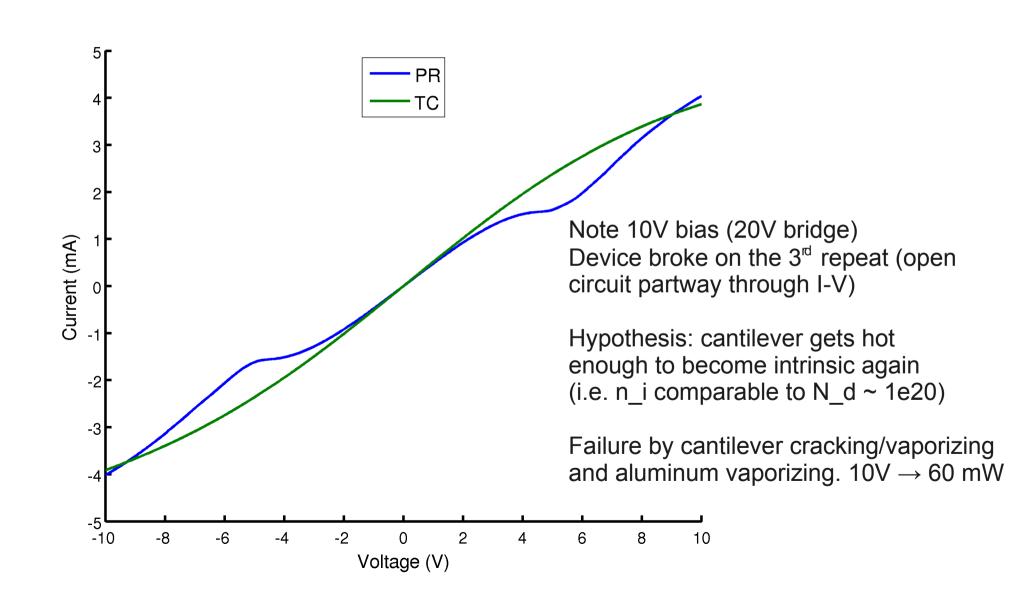


Resistance increase with voltage because mobility decreases with temperature

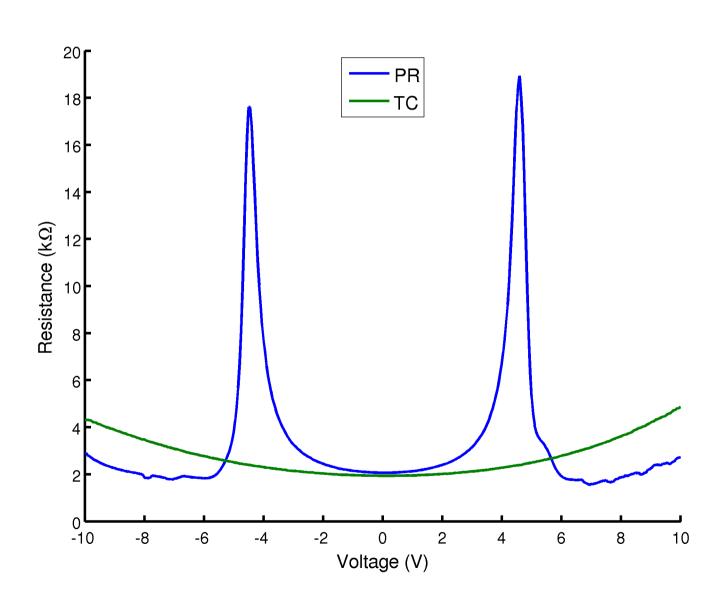
Temperature could be inferred from resistance (with calibration)

Cantilever reaches steadystate temperature faster than the analyzer steps from one voltage to another (same results whether V is swept or held at each voltage)

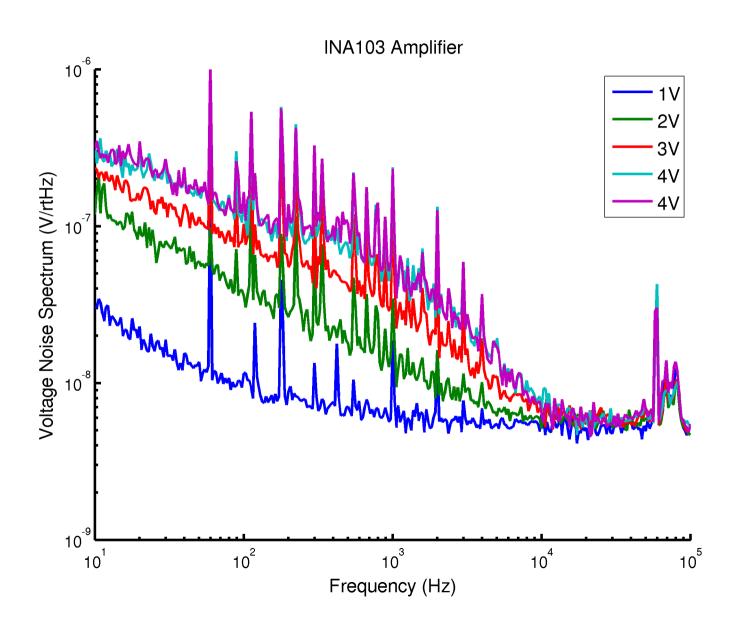
#### Thermal Breakdown



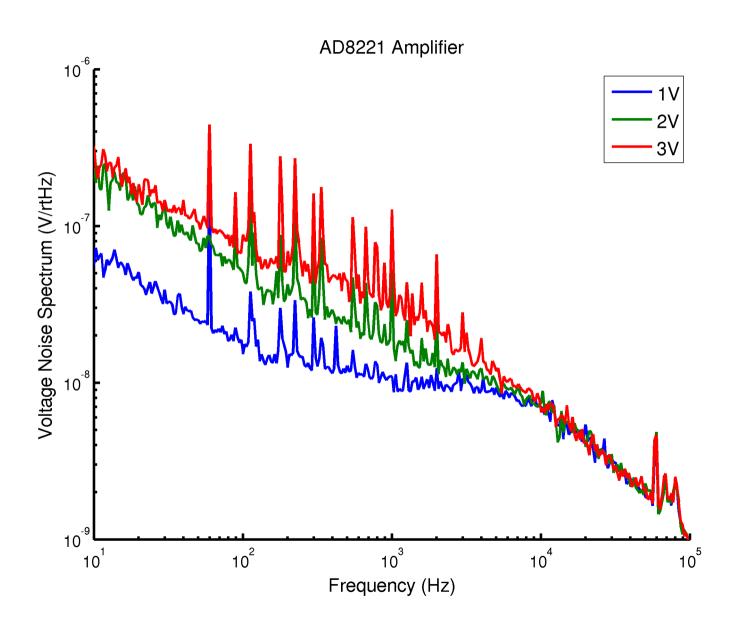
### Thermal Breakdown



### Noise w/ INA103, DC bias, 1000x gain



# Noise w/ AD8221, DC bias, 1000x gain



### Conclusions

- The resistance of the PR located on the cantilever deviates significantly from the TC resistor.
- Increased noise for small devices at large bias voltages.
- 1/f^n-esque near 10kHz but flattens out to 1/f at around 10 Hz. The noise is more of a lump than a trend in the data.
- Might not be an issue for my measurements (broadband high freq).
  Haven't compared the impact on resolution, i.e. integrated excess noise. Might be reduced in liquid. Still interesting.
- Things to look into eventually
  - Measure LDV spectrum vs. bias voltage (is the motion always there and just amplified by the larger bias)
  - Measure noise in vacuum (is fluid movement required)
  - Measure noise at elevated and reduced temperatures (reduce/increase temperature difference between the cantilever and ambient)